

N-channel 100 V, 19 mΩ logic level MOSFET in LFPAK56 4 November 2016 Product data sheet

1. **General description**

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product is designed and qualified for use in a wide range of power supply & motor control equipment.

Features and benefits 2.

- Advanced TrenchMOS provides low R_{DSon} and low gate charge •
- Logic level gate operation
- Avalanche rated, 100 % tested •
- LFPAK provides maximum power density in a Power SO8 package

Applications 3.

- Synchronous rectification in power supply equipment
- Chargers & adaptors with V_{out} < 10 V
- Fast charge & USB-PD applications
- Battery powered motor control
- LED lighting & TV backlight

4. Quick reference data

Table 1. Qu	iick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	56	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	167	W
Static charac	teristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	14.6	19	mΩ
Dynamic cha	racteristics					
Q _{GD}	gate-drain charge	$I_D = 15 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 13}; \text{ Fig. 14}$	-	14.1	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source		G-UFT4
4	G	gate	ប្រុប្បុ	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information							
Type number	Package	è					
	Name	Description	Version				
PSMN019-100YL	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN019-100YL	19L100

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	I	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	100	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	100	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	167	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	56	А
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	40	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3		-	226	А
T _{stg}	storage temperature			-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
Т _ј	junction temperature			-55	175	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C		-	56	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	226	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 56 A; V _{sup} ≤ 100 V; R _{GS} = 50 Ω; V _{GS} = 5 V; T _{j(init)} = 25 °C; unclamped; Fig. 4	[1][2]	-	94.1	mJ

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[2] Refer to application note AN10273 for further information.

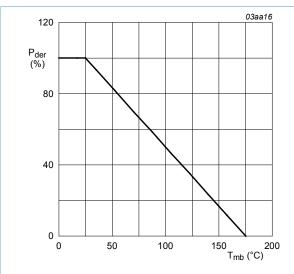


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

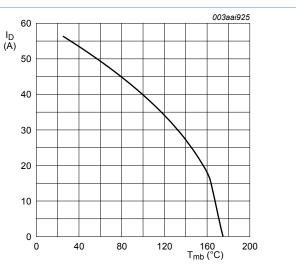
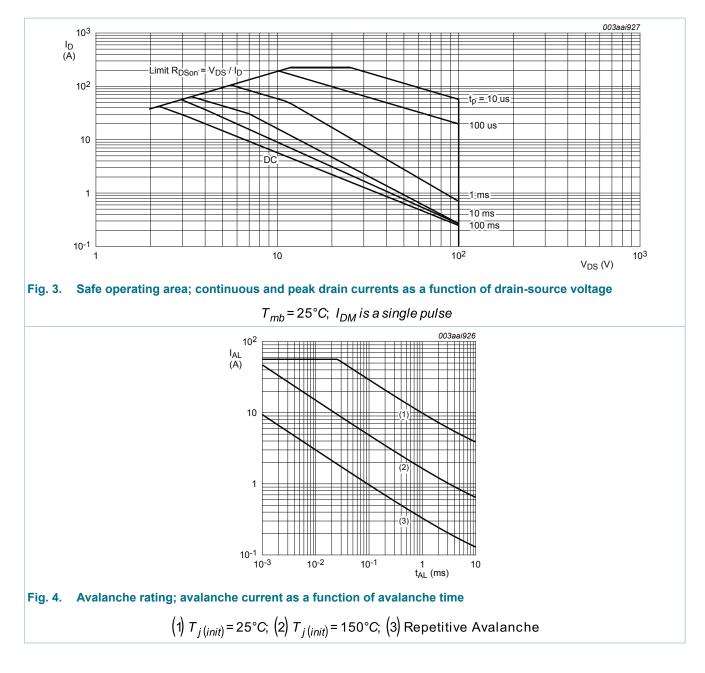


Fig. 2. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 5V$

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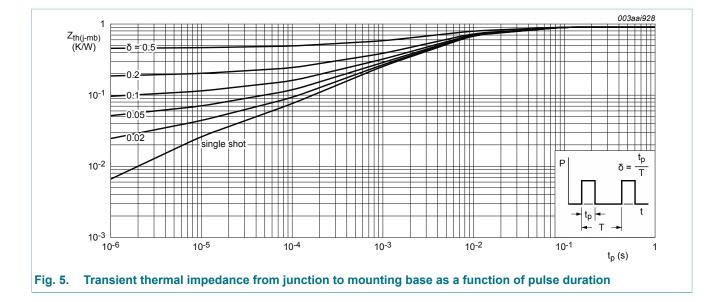
9. Thermal characteristics

Table 6. Th	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	-	0.9	K/W

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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·	I			
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	90	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C; <u>Fig. 9;</u> Fig. 10	1.4	1.7	2.1	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; <u>Fig. 9</u>	-	-	2.45	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 9</u>	0.5	-	-	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.04	10	μA
I _{GSS} ga	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	14.6	19	mΩ
	resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 11	-	14	18	mΩ
		V _{GS} = 5 V; I _D = 15 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	52.4	mΩ
Dynamic cl	naracteristics	· · ·				
Q _{G(tot)}	total gate charge	I _D = 15 A; V _{DS} = 80 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	72.4	-	nC
		I _D = 15 A; V _{DS} = 80 V; V _{GS} = 5 V;	-	39	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13;</u> <u>Fig. 14</u>	-	8.5	-	nC

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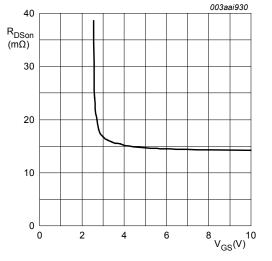
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Q _{GD}	gate-drain charge		-	14.1	-	nC
C _{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;	-	3814	5085	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	222	266	pF
C _{rss}	reverse transfer capacitance	-	-	133	182	pF
t _{d(on)}	turn-on delay time	V_{DS} = 80 V; R _L = 5 Ω; V _{GS} = 5 V; R _{G(ext)} = 5 Ω; T _j = 25 °C	-	18.5	-	ns
t _r	rise time		-	36.8	-	ns
t _{d(off)}	turn-off delay time	_	-	59.6	-	ns
t _f	fall time	-	-	34.3	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	I_{S} = 15 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	I _S = 15 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	38	-	ns

V_{DS} = 25 V; T_i = 25 °C

	S.		
		003aai929	
150		V _{GS} (V) = 10	40 R _{DSon}
I _D (А)		4.5	R _{DSon} (mΩ)
100		3	30
			20
		2.8	20
50		2.6	10
0		2.4	0
0	1 2	3 V _{DS} (V) 4	0
T _j = 25	°C; t _p = 300 μs		Fig. 7. Drain-



recovered charge



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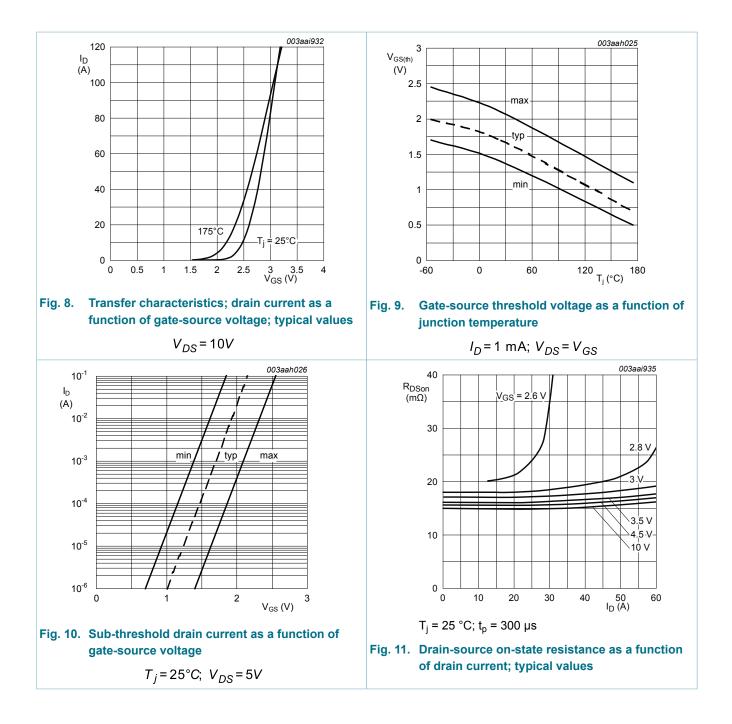
Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 15A$

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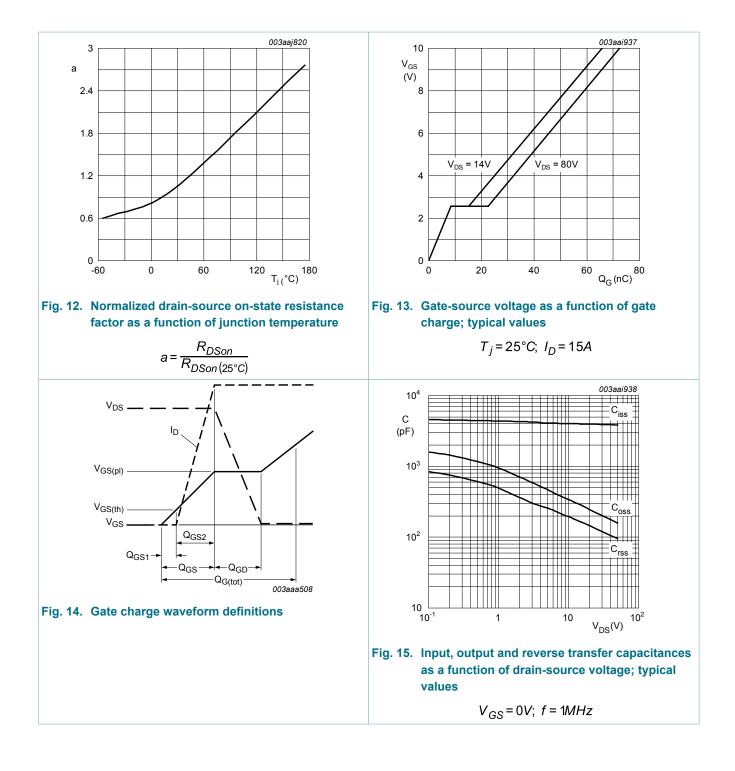
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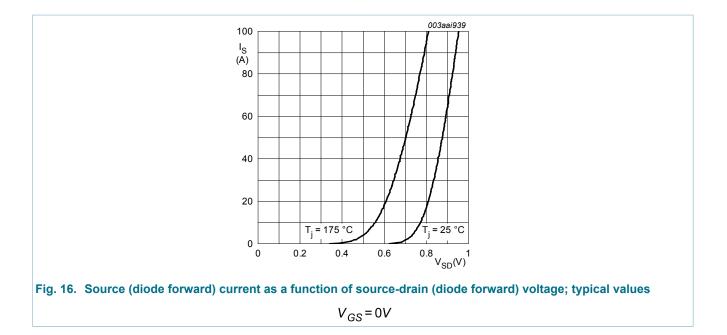
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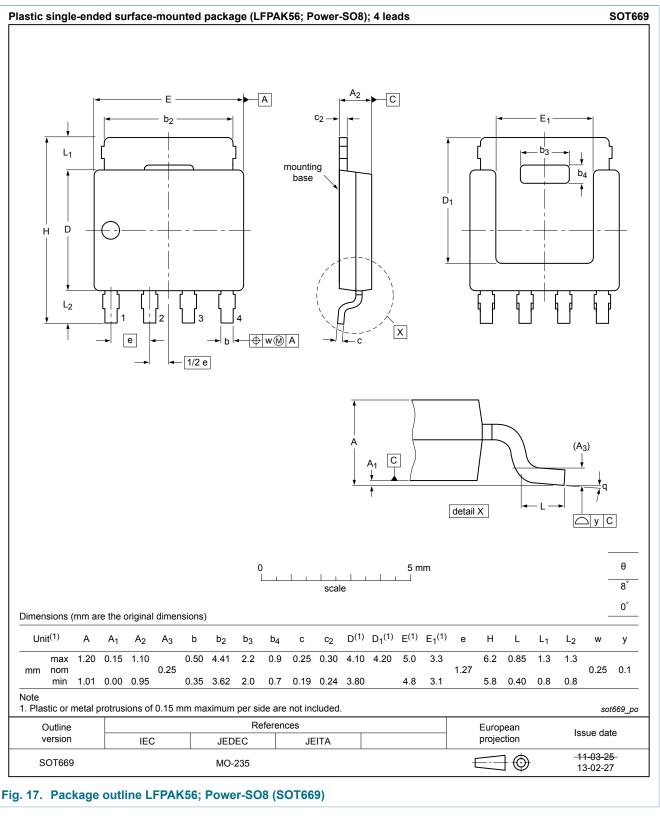
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11. Package outline



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